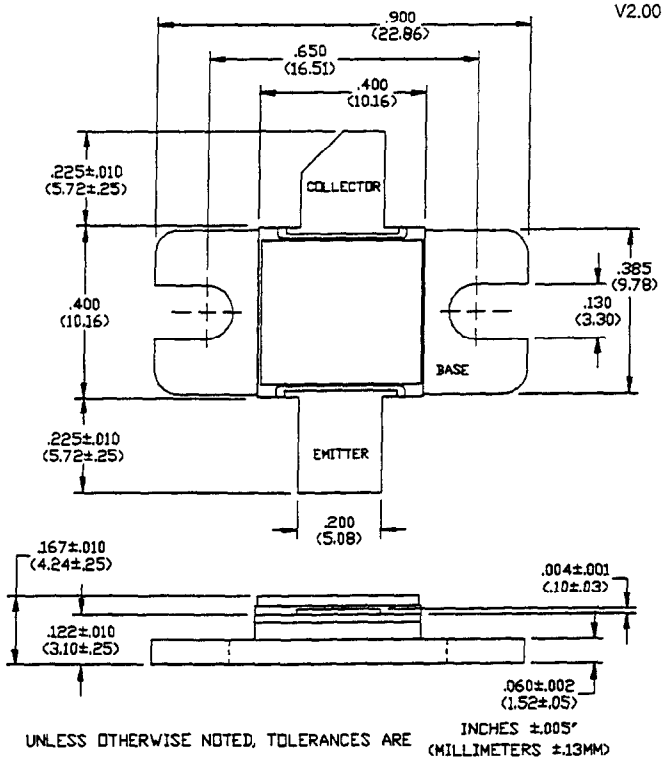
Radar Pulsed Power Transistor, 65W, 100µs Pulse, 10% Duty
3.1 - 3.4 GHz PH3134-65M

V2.00

Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package



Absolute Maximum Ratings at 25°C

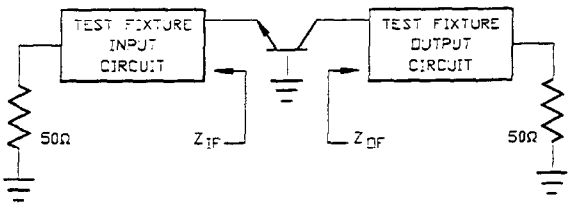
Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	7.7	A
Total Power Dissipation	P_{TOT}	350	W
Junction Temperature	T_J	200	°C
Storage Temperature	T_{STG}	-65 to +200	°C

Electrical Characteristics at 25°C

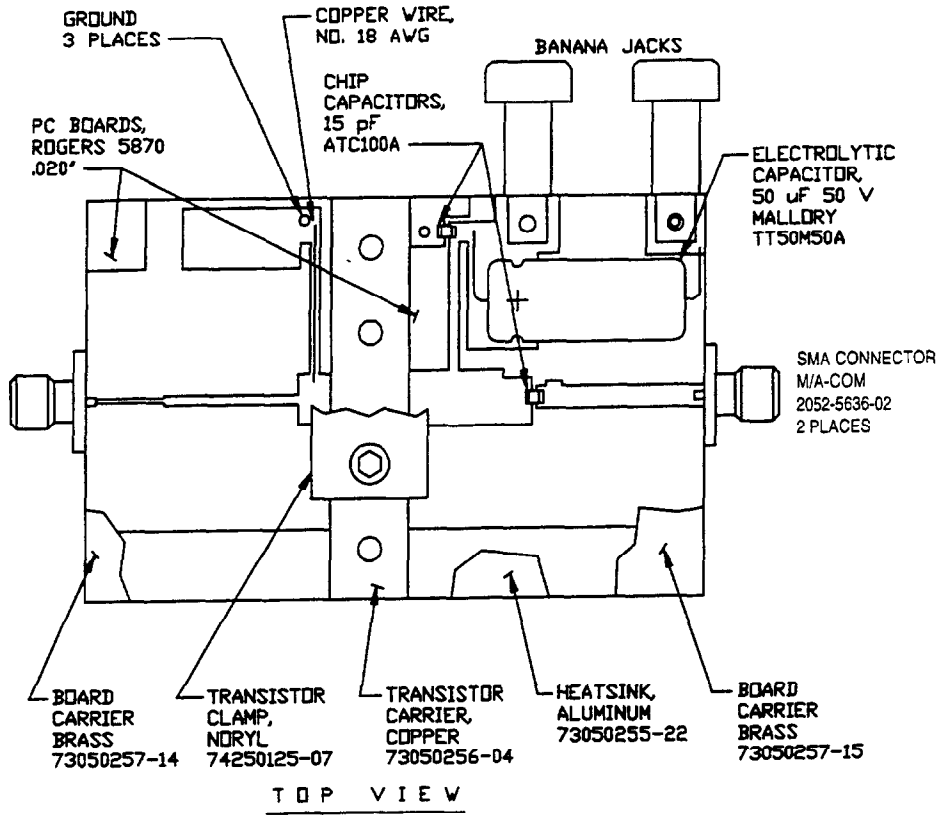
Parameter	Symbol	Min	Max	Units	Test Conditions
Collector-Emitter Breakdown Voltage	BV_{CES}	65	-	V	I_C=25 mA
Collector-Emitter Leakage Current	I_{CES}	-	5.0	mA	V_{CE}=36 V
Thermal Resistance	$R_{TH(JC)}$	-	0.5	°C/W	V_{CC}=36 V, P_{OUT}=65 W, F=3.10, 3.25, 3.40 GHz
Input Power	P_{IN}	-	11.6	W	V_{CC}=36 V, P_{OUT}=65 W, F=3.10, 3.25, 3.40 GHz
Power Gain	G_P	7.5	-	dB	V_{CC}=36 V, P_{OUT}=65 W, F=3.10, 3.25, 3.40 GHz
Collector Efficiency	η_C	35	-	%	V_{CC}=36 V, P_{OUT}=65 W, F=3.10, 3.25, 3.40 GHz
Input Return Loss	RL	6	-	dB	V_{CC}=36 V, P_{OUT}=65 W, F=3.10, 3.25, 3.40 GHz
Load Mismatch Tolerance	VSWR-T	-	2:1	-	V_{CC}=36 V, P_{OUT}=65 W, F=3.25 GHz

Broadband Test Fixture Impedances

F(GHz)	$Z_{IF}(\Omega)$	$Z_{OF}(\Omega)$
3.10	11.2 - j11.7	8.1 - j5.3
3.25	11.5 - j9.5	7.1 - j4.3
3.40	12.7 - j7.6	6.4 - j3.3



RF Test Fixture



Test Fixture PC Board Dimensions